

1 **Supporting Information**

2 **Void-rich layered SiGe_x alloys via in situ molten salt**
3 **electrochemistry for high-performance lithium-ion battery anodes**

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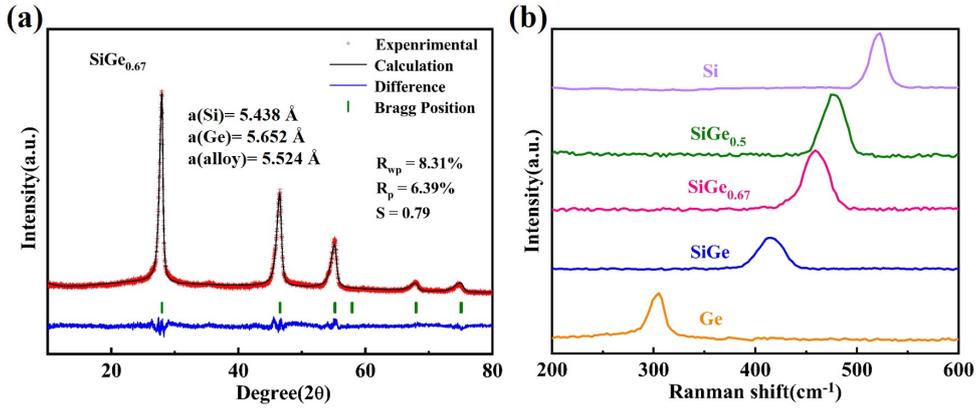
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2 **Fig. S1** (a) Rietveld refinement of XRD patterns for SiGe_{0.67}. (b) Raman results of Si, Ge and
3 SiGe_x alloys with various ratios.

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5 **Calculation of Ge Content from Refined Lattice Parameters Using Vegard's Law:**

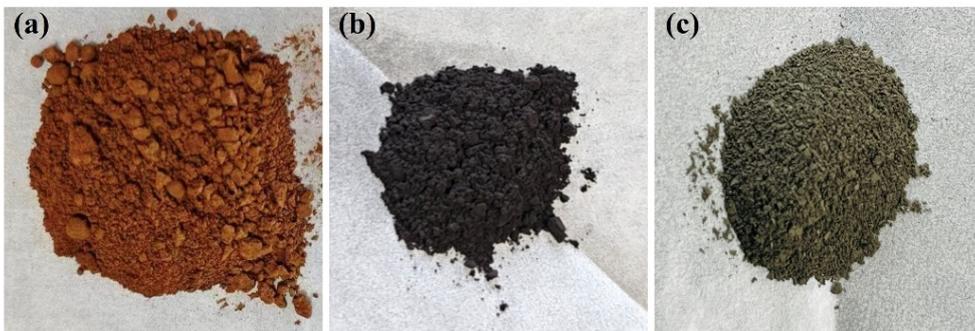
6 The refined lattice parameters are as follows: $a(\text{Si}) = 5.438 \text{ \AA}$, $a(\text{Ge}) = 5.652 \text{ \AA}$, and
7 $a(\text{alloy}) = 5.524 \text{ \AA}$ for the SiGe_x sample. Applied the complete form of Vegard's law,
8 which accounts for the total atomic fraction in the Si₁Ge_x system:

9
$$a(\text{alloy}) = \frac{1}{1+x} \times a(\text{Si}) + \frac{x}{1+x} \times a(\text{Ge})$$
 Solving this equation with the refined values

10 yields a germanium content of $x \approx 0.67$, corresponding to a composition of SiGe_{0.67}.

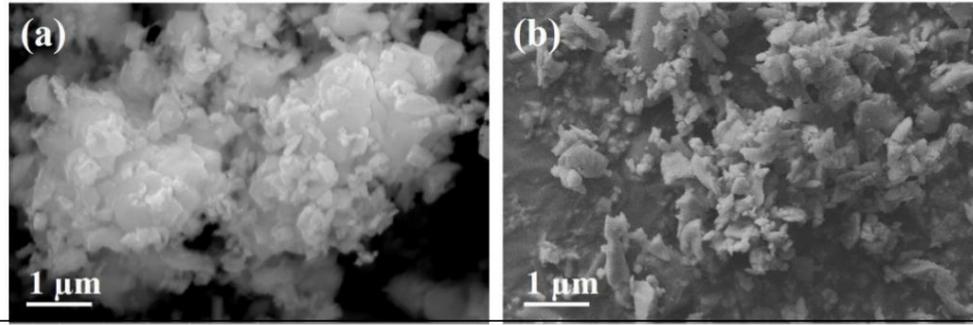
11 This result, which provides a precise quantification of the Ge content.

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14 **Fig. S2** Optical image of (a) Pristine SiO; (b) Ge powder; (c) Electrolysis product SiGe_{0.67}



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2 **Fig. S3** SEM images of (a) Ge powder, (b) SiO particles.

3 **Table S1** Atomic ratio of elements in SiGe_{0.67}

Element	Family	Atomic	Atomic	Mass	Mass	Fit
		Fraction(%)	Error(%)	Fraction(%)	Error(%)	error(%)
Si	K	59.41	7.76	37.01	3.08	0.33
Ge	K	40.59	7.29	62.99	9.78	0.14

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5 **Table S2** Comparison of the initial Coulombic efficiency and cycling stability of the
6 SiGe_{0.67} anode with other silicon-based composite materials.

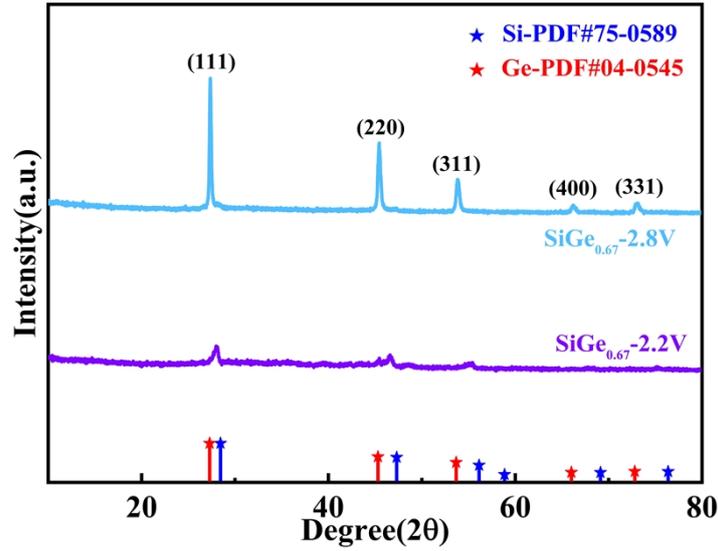
Samples	ICE(%)	Rate Performance	Cycling Stability	Ref.
		(mAh g ⁻¹)	(mAh g ⁻¹)	
SiGe nanowire	86.8	625.5 @4 A g ⁻¹	1500 after 270 cycles @1 A g ⁻¹	S1
p-Si/CNT	52.8	532.4 @5 A g ⁻¹	796 after 100 cycles @0.5 A g ⁻¹	S2
Si@C@Si	52.8	1000 @1 A g ⁻¹	904 after 100 cycles @0.5 A g ⁻¹	S3
Si nanowire	76	521 @2 A g ⁻¹	905 after 200 @1A g ⁻¹	S4
porous Si@C	76.4	600 @4 A g ⁻¹	630 after 100 cycles @0.84 A g ⁻¹	S5
Si nanotube	76.4	1362 @5 A g ⁻¹	950 after 200 @1 A g ⁻¹	S6

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2 DFT Calculation Methods:

3 We have employed the first-principles [7,8] to perform density functional theory
4 (DFT) calculations within the generalized gradient approximation (GGA) using the
5 Perdew-Burke-Ernzerhof (PBE) [9] formulation. We have chosen the projected
6 augmented wave (PAW) potentials [10,11] to describe the ionic cores and take valence
7 electrons into account using a plane wave basis set with a kinetic energy cutoff of 520
8 eV. Partial occupancies of the Kohn–Sham orbitals were allowed using the Gaussian
9 smearing method with a width of 0.05 eV. The electronic energy was considered self-
10 consistent when the energy change was smaller than 10⁻⁵ eV. A geometry optimization
11 was considered convergent when the force change was smaller than 0.03 eV Å⁻¹. The
12 Brillouin zone integration is performed using 3×1×1 Gamma centered grids k-point
13 sampling for a structure.

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Fig. S4 XRD patterns of the electrochemical products obtained at different voltages.

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4 **The Li^+ diffusion coefficients D_{Li^+} calculation:**

5 The Li^+ diffusion coefficients D_{Li^+} of the electrode is calculated based on eqns. (1)

6 and eqns. (2):

$$7 \quad D_{\text{Li}^+} = \frac{R^2 T^2}{2A^2 n^4 F^4 C^2 \sigma^2} \quad (1)$$

$$8 \quad Z' = R_0 + \sigma \omega^{-1/2} \quad (2)$$

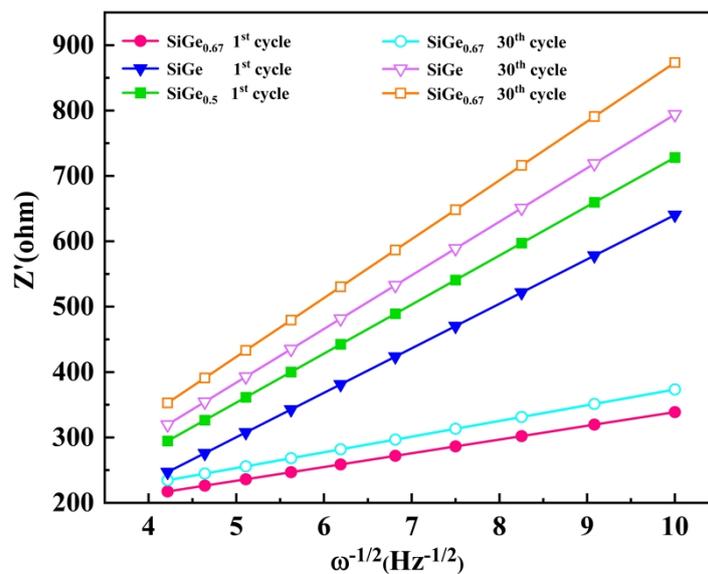
9 where R , T and F stand for the gas constant, absolute temperature and Faraday constant,

10 respectively. A , n and C signify the surface area of electrode, number of electrons per

11 molecule during oxidation and concentration of lithium ions, respectively. The σ

12 denotes the Warburg factor which can be fitted out based on linear curve of $\omega^{-1/2} \sim Z'$.

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Fig. S5 The linear relationship of $\omega^{-1/2} \sim Z'$.

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Table S3 Summary of the fitted value of EIS spectra

Sample	Cycles	R_{SEI} (ohm)	R_{ct} (ohm)	σ	$D_{Li^+} \times 10^{-11}$ (cm ² s ⁻¹)
SiGe	1 st cycle	72.8	141.7	68	0.16
	30 th cycle	110.2	170.3	82	0.11
SiGe _{0.67}	1 st cycle	28.7	45.4	21	1.71
	30 th cycle	47.1	56.8	24	1.31
SiGe _{0.5}	1 st cycle	89.1	121.5	75	0.13
	30 th cycle	142.4	180.6	90	0.09

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